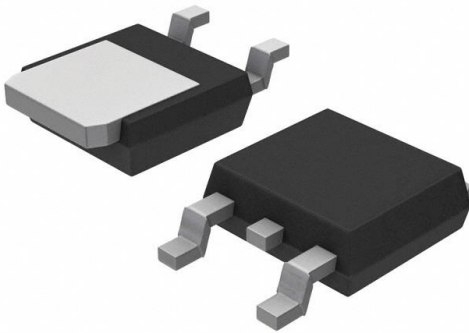


MJD50G Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	MJD50G-DG
Manufacturer	onsemi
Manufacturer Product Number	MJD50G
Description	TRANS NPN 400V 1A DPAK
Detailed Description	Bipolar (BJT) Transistor NPN 400 V 1 A 10MHz 1.56 W Surface Mount DPAK



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

MJD50G

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

400 V

Current - Collector Cutoff (Max):

200 μ A

Power - Max:

1.56 W

Operating Temperature:

-65°C ~ 150°C (TJ)

Package / Case:

TO-252-3, DPAK (2 Leads + Tab), SC-63

Base Product Number:

MJD50

Manufacturer:

onsemi

Product Status:

Active

Current - Collector (Ic) (Max):

1 A

Vce Saturation (Max) @ Ib, Ic:

1V @ 200mA, 1A

DC Current Gain (hFE) (Min) @ Ic, Vce:

30 @ 300mA, 10V

Frequency - Transition:

10MHz

Mounting Type:

Surface Mount

Supplier Device Package:

DPAK

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

High Voltage Power Transistors

DPAK for Surface Mount Applications

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

Designed for line operated audio output amplifier, switchmode supply drivers and other switching applications.

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically Similar to Popular TIP47, and TIP50
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

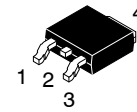
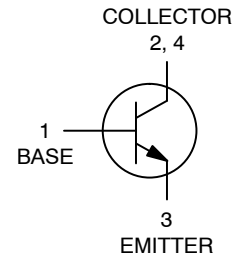
MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V_{CEO}	250 400	Vdc
Collector-Base Voltage MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	V_{CB}	350 500	Vdc
Emitter-Base Voltage	V_{EB}	5	Vdc
Collector Current - Continuous	I_C	1	Adc
Collector Current - Peak	I_{CM}	2	Adc
Base Current	I_B	0.6	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	W W/ $^\circ\text{C}$
Total Power Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	1.56 0.0125	W W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
ESD - Human Body Model	HBM	3B	V
ESD - Machine Model	MM	C	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

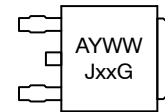
1. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

**NPN SILICON POWER
TRANSISTORS**
1 AMPERE
250, 400 VOLTS, 15 WATTS



**DPAK
CASE 369C
STYLE 1**

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- Jxx = Device Code
xx = 47 or 50
- G = Pb-Free Package

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	8.33	$^{\circ}\text{C}/\text{W}$
Thermal Resistance Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	$^{\circ}\text{C}/\text{W}$
Lead Temperature for Soldering Purpose	T_L	260	$^{\circ}\text{C}$

2. These ratings are applicable when surface mounted on the minimum pad sizes recommended.

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
----------------	--------	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 30 \text{ mAdc}$, $I_B = 0$) MJD47, NJVMJD47T4G MJD50, NJVMJD50T4G	$V_{CE(sus)}$	250 400	- -	Vdc
Collector Cutoff Current ($V_{CE} = 150 \text{ Vdc}$, $I_B = 0$) MJD47, NJVMJD47T4G ($V_{CE} = 300 \text{ Vdc}$, $I_B = 0$) MJD50, NJVMJD50T4G	I_{CEO}	- -	0.2 0.2	mAdc
Collector Cutoff Current ($V_{CE} = 350 \text{ Vdc}$, $V_{BE} = 0$) MJD47, NJVMJD47T4G ($V_{CE} = 500 \text{ Vdc}$, $V_{BE} = 0$) MJD50, NJVMJD50T4G	I_{CES}	- -	0.1 0.1	mAdc
Emitter Cutoff Current ($V_{BE} = 5 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	1	mAdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = 0.3 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$) ($I_C = 1 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$)	h_{FE}	30 10	150 -	-
Collector-Emitter Saturation Voltage ($I_C = 1 \text{ Adc}$, $I_B = 0.2 \text{ Adc}$)	$V_{CE(sat)}$	-	1	Vdc
Base-Emitter On Voltage ($I_C = 1 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$)	$V_{BE(on)}$	-	1.5	Vdc

DYNAMIC CHARACTERISTICS

Current Gain – Bandwidth Product ($I_C = 0.2 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 2 \text{ MHz}$)	f_T	10	-	MHz
Small-Signal Current Gain ($I_C = 0.2 \text{ Adc}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1 \text{ kHz}$)	h_{fe}	25	-	-

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

TYPICAL CHARACTERISTICS

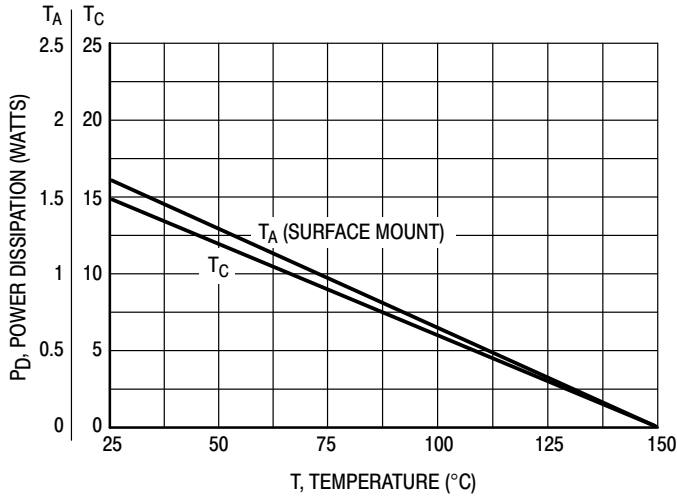


Figure 1. Power Derating

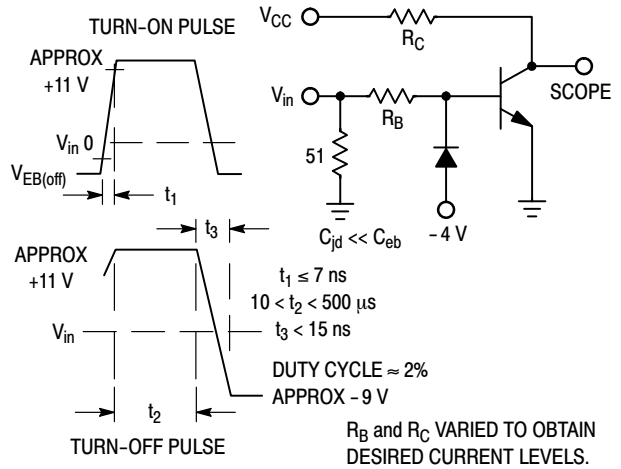


Figure 2. Switching Time Equivalent Circuit

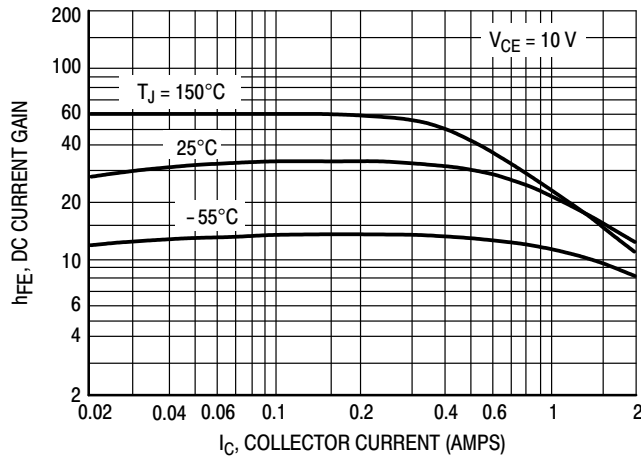


Figure 3. DC Current Gain

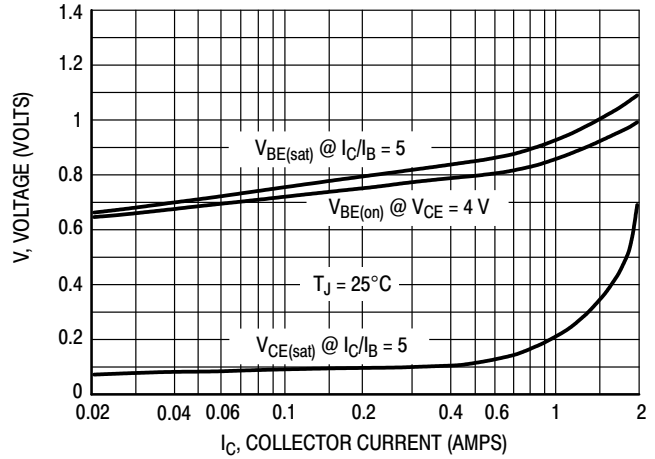


Figure 4. "On" Voltages

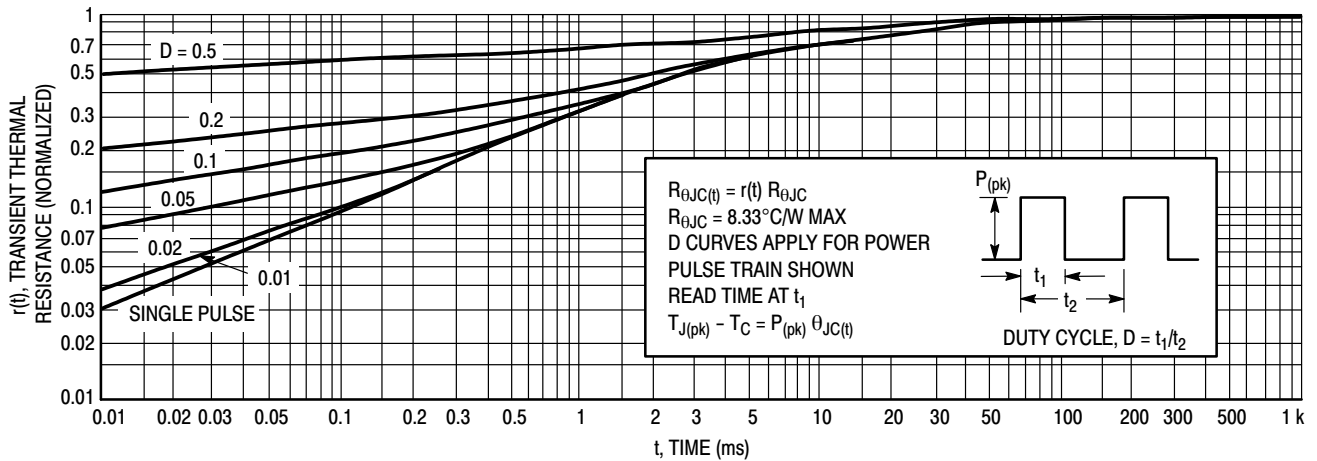


Figure 5. Thermal Response

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G

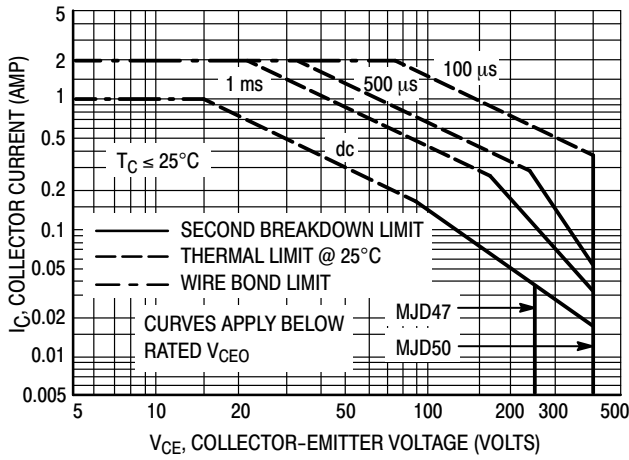


Figure 6. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 6 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 5. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

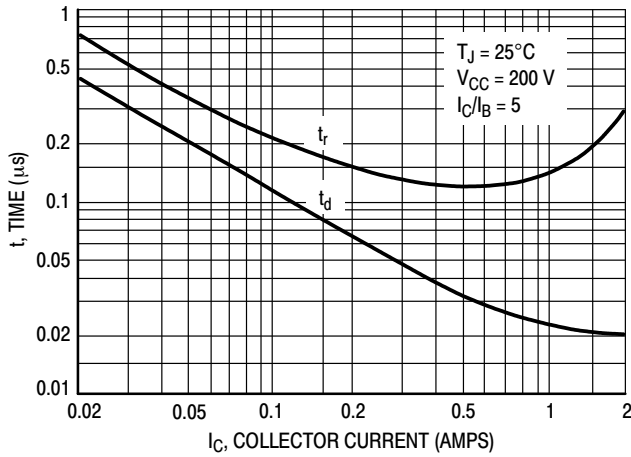


Figure 7. Turn-On Time

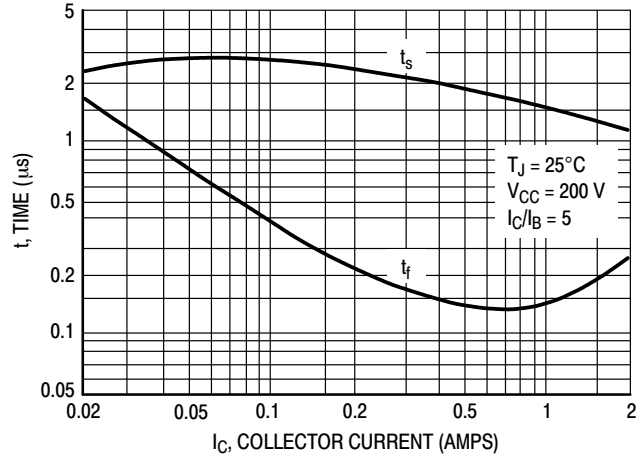


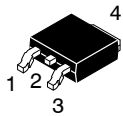
Figure 8. Turn-Off Time

MJD47, NJVMJD47T4G, MJD50, NJVMJD50T4G**ORDERING INFORMATION**

Device	Package	Shipping[†]
MJD47G	369C (Pb-Free)	75 Units / Rail
MJD47T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD47T4G*	369C (Pb-Free)	2,500 / Tape & Reel
MJD50G	369C (Pb-Free)	75 Units / Rail
MJD50T4G	369C (Pb-Free)	2,500 / Tape & Reel
NJVMJD50T4G*	369C (Pb-Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

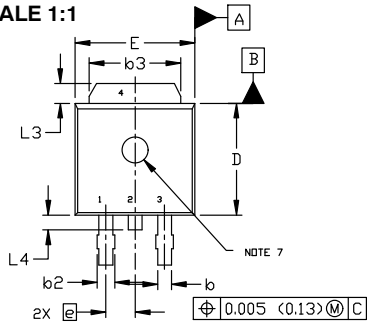
*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



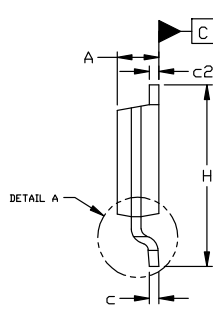
DPAK (SINGLE GAUGE)
CASE 369C
ISSUE G

DATE 31 MAY 2023

SCALE 1:1



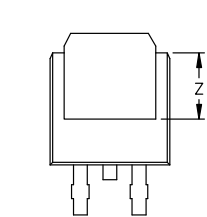
TOP VIEW



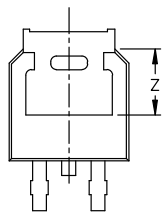
SIDE VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3, AND Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

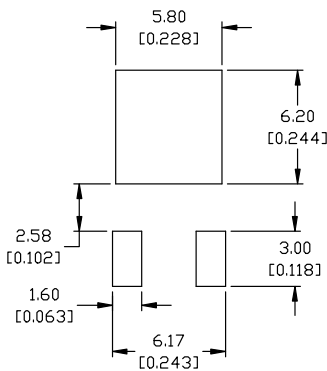


BOTTOM VIEW



BOTTOM VIEW

ALTERNATE CONSTRUCTIONS

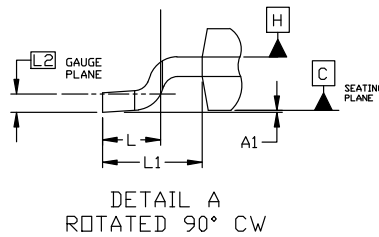


RECOMMENDED MOUNTING FOOTPRINT*

*FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

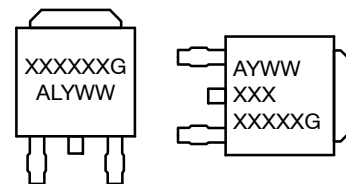
- | | | | | |
|--|--|---|---|--|
| <p>STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> | <p>STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN</p> | <p>STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE</p> | <p>STYLE 4:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE</p> | <p>STYLE 5:
PIN 1. GATE
2. ANODE
3. CATHODE
4. ANODE</p> |
| <p>STYLE 6:
PIN 1. MT1
2. MT2
3. GATE
4. MT2</p> | <p>STYLE 7:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR</p> | <p>STYLE 8:
PIN 1. N/C
2. CATHODE
3. ANODE
4. CATHODE</p> | <p>STYLE 9:
PIN 1. ANODE
2. CATHODE
3. RESISTOR ADJUST
4. CATHODE</p> | <p>STYLE 10:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. ANODE</p> |

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114	REF	2.90	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---



DETAIL A
ROTATED 90° CW

GENERIC MARKING DIAGRAM*



- IC** **Discrete**
- XXXXXX = Device Code
 A = Assembly Location
 L = Wafer Lot
 Y = Year
 WW = Work Week
 G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	DPAK (SINGLE GAUGE)	PAGE 1 OF 1

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ONLINE SUPPORT: www.onsemi.com/support

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OUR CERTIFICATE

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